

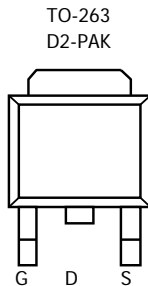
**AOB436**  
**N-Channel Enhancement Mode Field Effect Transistor**

**General Description**

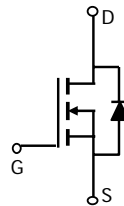
The AOB436 uses advanced trench technology and design to provide excellent  $R_{DS(ON)}$  with low gate charge. This device is suitable for use in PWM, load switching and general purpose applications. Standard product AOB436 is Pb-free (meets ROHS & Sony 259 specifications). AOB436L is a Green Product ordering option. AOB436 and AOB436L are electrically identical.

**Features**

$V_{DS}$  (V) = 25V  
 $I_D$  = 55A ( $V_{GS}$  = 10V)  
 $R_{DS(ON)} < 7 \text{ m}\Omega$  ( $V_{GS}$  = 10V)  
 $R_{DS(ON)} < 11 \text{ m}\Omega$  ( $V_{GS}$  = 4.5V)



TO-263  
 D2-PAK  
 Top View  
 Drain Connected to  
 Tab


**Absolute Maximum Ratings  $T_A=25^\circ\text{C}$  unless otherwise noted**

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	$V_{DS}$	25	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Continuous Drain Current <sup>G</sup>	$I_D$	$T_C=25^\circ\text{C}$	A
		$T_C=100^\circ\text{C}$	
Pulsed Drain Current <sup>C</sup>	$I_{DM}$	150	
Avalanche Current <sup>C</sup>	$I_{AR}$	30	A
Repetitive avalanche energy $L=0.1\text{mH}$ <sup>C</sup>	$E_{AR}$	45	mJ
Power Dissipation <sup>B</sup>	$P_D$	$T_C=25^\circ\text{C}$	W
		$T_C=100^\circ\text{C}$	
Power Dissipation <sup>A</sup>	$P_{DSM}$	$T_A=25^\circ\text{C}$	W
		$T_A=70^\circ\text{C}$	
Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 to 175	$^\circ\text{C}$

**Thermal Characteristics**

Parameter	Symbol	Typ	Max	Units
Maximum Junction-to-Ambient <sup>A</sup>	$R_{\theta JA}$	10	15	$^\circ\text{C/W}$
Maximum Junction-to-Ambient <sup>A</sup>		Steady-State	41	50
Maximum Junction-to-Case <sup>B</sup>	$R_{\theta JC}$	1.9	3	$^\circ\text{C/W}$

Electrical Characteristics ( $T_J=25^\circ\text{C}$  unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
<b>STATIC PARAMETERS</b>						
$BV_{DSS}$	Drain-Source Breakdown Voltage	$I_D=250\mu\text{A}$ , $V_{GS}=0\text{V}$	25			V
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS}=20\text{V}$ , $V_{GS}=0\text{V}$ $T_J=55^\circ\text{C}$			1	$\mu\text{A}$
					5	
$I_{GSS}$	Gate-Body leakage current	$V_{DS}=0\text{V}$ , $V_{GS}=\pm 20\text{V}$			100	nA
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}$ , $I_D=250\mu\text{A}$	1	1.8	3	V
$I_{D(ON)}$	On state drain current	$V_{GS}=10\text{V}$ , $V_{DS}=5\text{V}$	100			A
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS}=10\text{V}$ , $I_D=30\text{A}$ $T_J=125^\circ\text{C}$		5.7	7	m $\Omega$
				8		
			$V_{GS}=4.5\text{V}$ , $I_D=30\text{A}$	9	11	
$g_{FS}$	Forward Transconductance	$V_{DS}=5\text{V}$ , $I_D=30\text{A}$		53		S
$V_{SD}$	Diode Forward Voltage	$I_S=1\text{A}$ , $V_{GS}=0\text{V}$		0.73	1	V
$I_S$	Maximum Body-Diode Continuous Current				50	A
<b>DYNAMIC PARAMETERS</b>						
$C_{iss}$	Input Capacitance	$V_{GS}=0\text{V}$ , $V_{DS}=12.5\text{V}$ , $f=1\text{MHz}$		1850	2220	pF
$C_{oss}$	Output Capacitance			472		pF
$C_{rss}$	Reverse Transfer Capacitance			275		pF
$R_g$	Gate resistance	$V_{GS}=0\text{V}$ , $V_{DS}=0\text{V}$ , $f=1\text{MHz}$		0.86	1.5	$\Omega$
<b>SWITCHING PARAMETERS</b>						
$Q_g(10\text{V})$	Total Gate Charge	$V_{GS}=10\text{V}$ , $V_{DS}=12.5\text{V}$ , $I_D=30\text{A}$		34	40	nC
$Q_g(4.5\text{V})$	Total Gate Charge			16.8		nC
$Q_{gs}$	Gate Source Charge			7		nC
$Q_{gd}$	Gate Drain Charge			8.5		nC
$t_{D(on)}$	Turn-On DelayTime			7.5		ns
$t_r$	Turn-On Rise Time	$V_{GS}=10\text{V}$ , $V_{DS}=12.5\text{V}$ , $R_L=0.39\Omega$ , $R_{GEN}=3\Omega$		33		ns
$t_{D(off)}$	Turn-Off DelayTime			25		ns
$t_f$	Turn-Off Fall Time			22		ns
$t_{rr}$	Body Diode Reverse Recovery Time	$I_F=30\text{A}$ , $dI/dt=100\text{A}/\mu\text{s}$		32	38	ns
$Q_{rr}$	Body Diode Reverse Recovery Charge	$I_F=30\text{A}$ , $dI/dt=100\text{A}/\mu\text{s}$		19		nC

A: The value of  $R_{\theta JA}$  is measured with the device mounted on 1 in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with  $T_A=25^\circ\text{C}$ . The Power dissipation  $P_{DSM}$  is based on  $R_{\theta JA}$  and the maximum allowed junction temperature of  $150^\circ\text{C}$ . The value in any given application depends on the user's specific board design, and the maximum temperature of  $175^\circ\text{C}$  may be used if the PCB allows it.

B. The power dissipation  $P_D$  is based on  $T_{J(MAX)}=175^\circ\text{C}$ , using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.

C: Repetitive rating, pulse width limited by junction temperature  $T_{J(MAX)}=175^\circ\text{C}$ .

D. The  $R_{\theta JA}$  is the sum of the thermal impedance from junction to case  $R_{\theta JC}$  and case to ambient.

E. The static characteristics in Figures 1 to 6 are obtained using  $<300 \mu\text{s}$  pulses, duty cycle 0.5% max.

F. These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of  $T_{J(MAX)}=175^\circ\text{C}$ .

G. The maximum current rating is limited by bond-wires.

H. These tests are performed with the device mounted on 1 in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with  $T_A=25^\circ\text{C}$ . The SOA curve provides a single pulse rating.

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TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

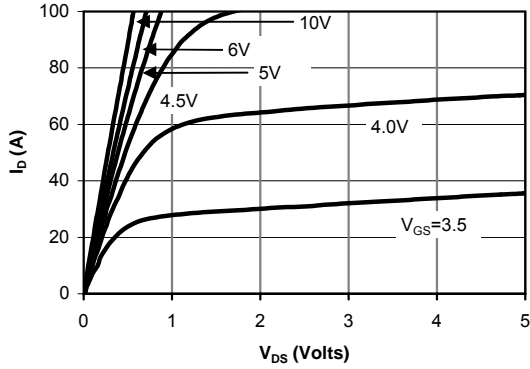


Fig 1: On-Region Characteristics

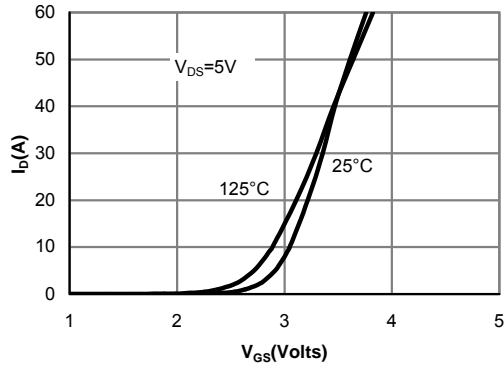


Figure 2: Transfer Characteristics

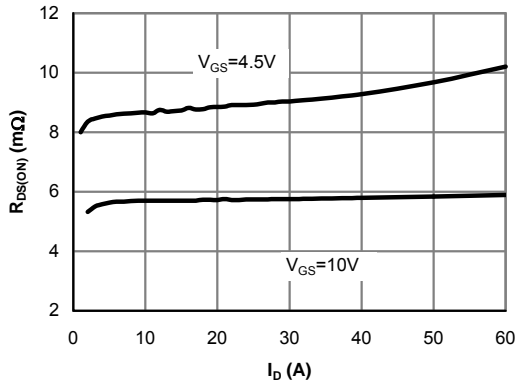


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

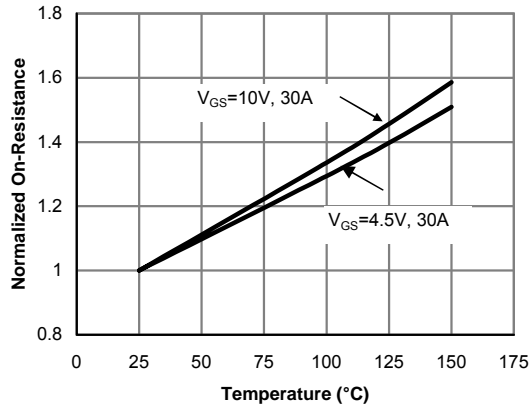


Figure 4: On-Resistance vs. Junction Temperature

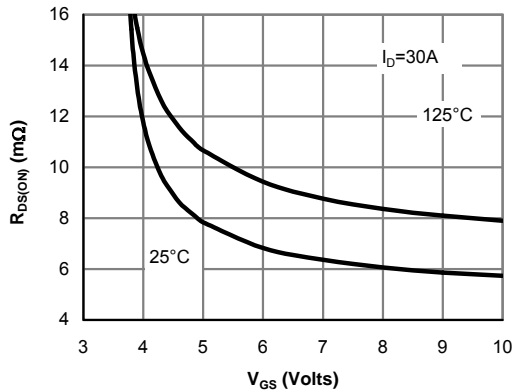


Figure 5: On-Resistance vs. Gate-Source Voltage

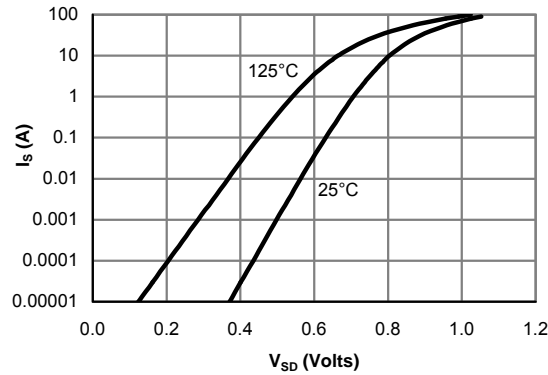


Figure 6: Body-Diode Characteristics

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

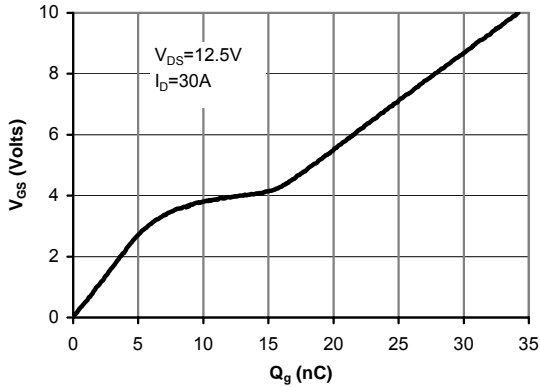


Figure 7: Gate-Charge Characteristics

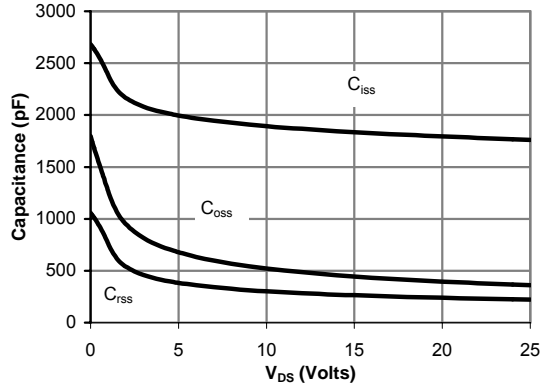


Figure 8: Capacitance Characteristics

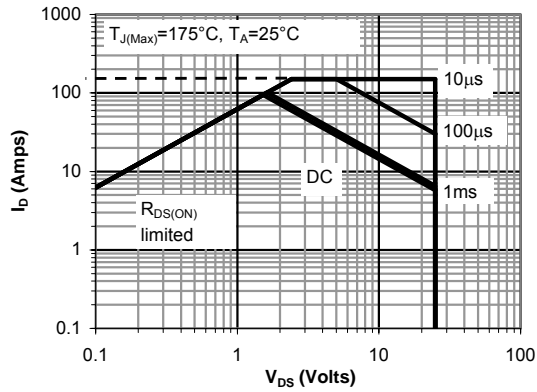


Figure 9: Maximum Forward Biased Safe Operating Area (Note E)

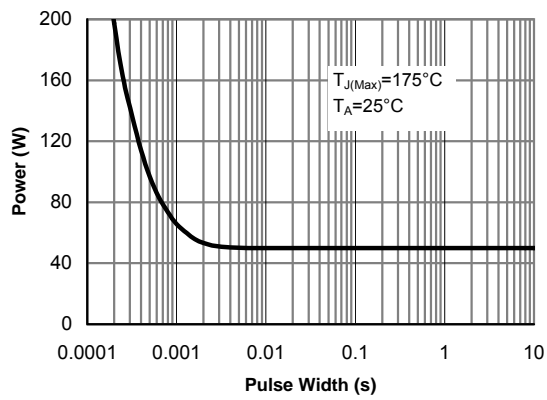


Figure 10: Single Pulse Power Rating Junction-to-Case (Note F)

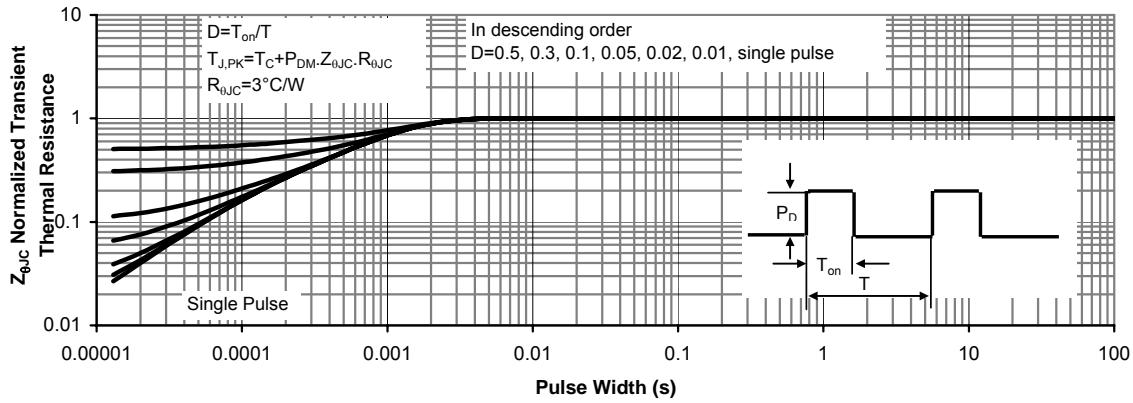


Figure 11: Normalized Maximum Transient Thermal Impedance (Note F)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

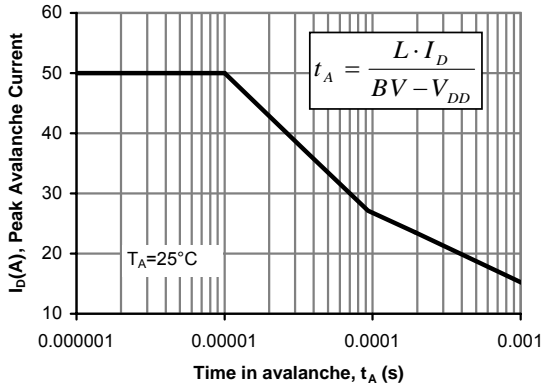


Figure 12: Single Pulse Avalanche capability

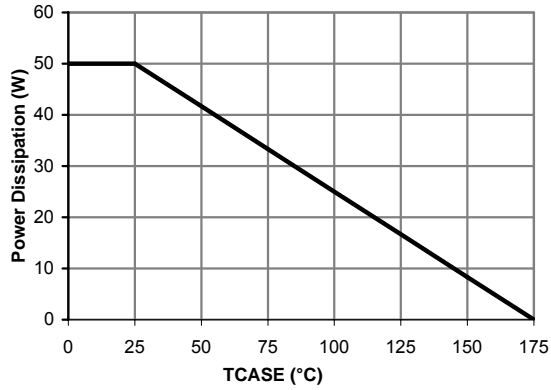


Figure 13: Power De-rating (Note B)

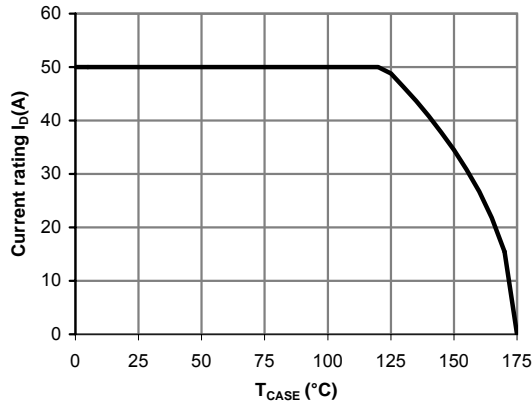


Figure 14: Current De-rating (Note B)

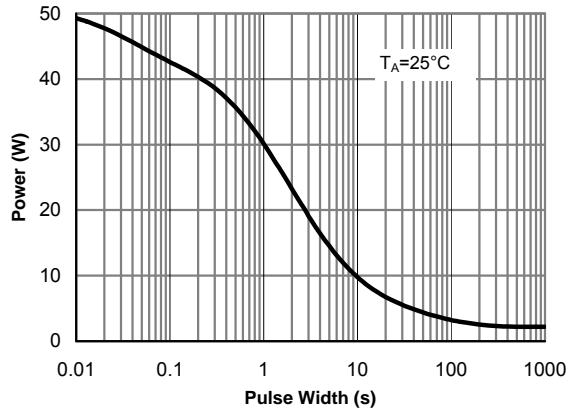


Figure 15: Single Pulse Power Rating Junction-to-Ambient (Note H)

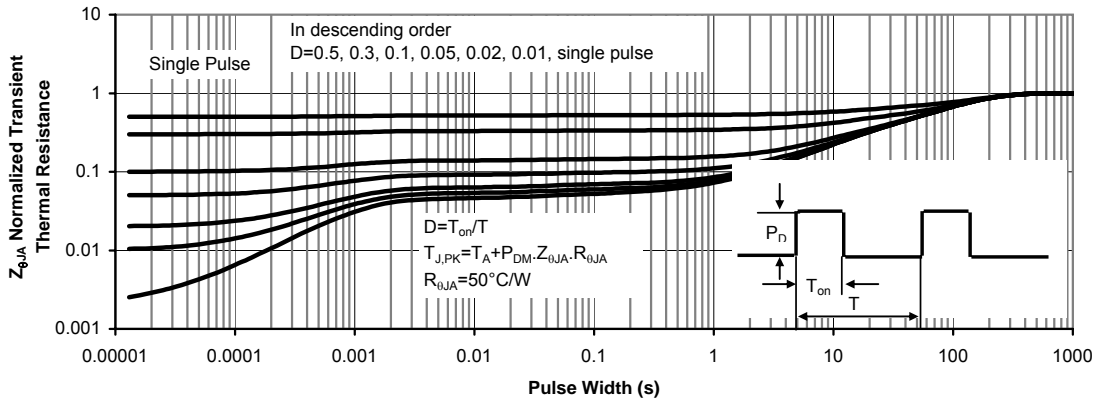


Figure 16: Normalized Maximum Transient Thermal Impedance (Note H)